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# Silicon Carbide Schottky Diode

1200 V, 20 A

# **NVDSH20120C**

## **Description**

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

#### **Features**

- Max Junction Temperature 175°C
- Avalanche Rated 166 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- NV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Halogen Free/BFR Free and are RoHS Compliant

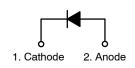
#### **Applications**

- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters



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**Schottky Diode** 



TO-247-2LD CASE 340DA

#### **MARKING DIAGRAM**



DSH20120C

77

C = Specific Device Code

= Assembly Plant Code

YWW = Date Code (Year & Week)

= Lot Code

## **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet

## **ABSOLUTE MAXIMUM RATINGS** ( $T_J = 25$ °C unless otherwise noted)

Symbol	Parameter		Value	Unit
$V_{RRM}$	Peak Repetitive Reverse Voltage		1200	V
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note 1)		166	mJ
lF	Continuous Rectified Forward Current @ T <sub>C</sub> < 149°C		20	Α
	Continuous Rectified Forward Current @ T <sub>C</sub> <	26	1	
I <sub>F, Max</sub>	Non-Repetitive Peak Forward Surge Current	T <sub>C</sub> = 25°C, 10 μs	896	Α
		T <sub>C</sub> = 150°C, 10 μs	854	А
I <sub>F,SM</sub>	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	119	А
I <sub>F,RM</sub>	Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	40	Α
Ptot	Power Dissipation	T <sub>C</sub> = 25°C	214	W
		T <sub>C</sub> = 150°C	35	W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. E<sub>AS</sub> of 166 mJ is based on starting T<sub>J</sub> = 25°C, L = 0.5 mH, I<sub>AS</sub> = 25.8 A, V = 50 V.

## THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{ heta JC}$	Thermal Resistance, Junction to Case, Max	0.7	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max	40	°C/W

## **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ unless otherwise noted)

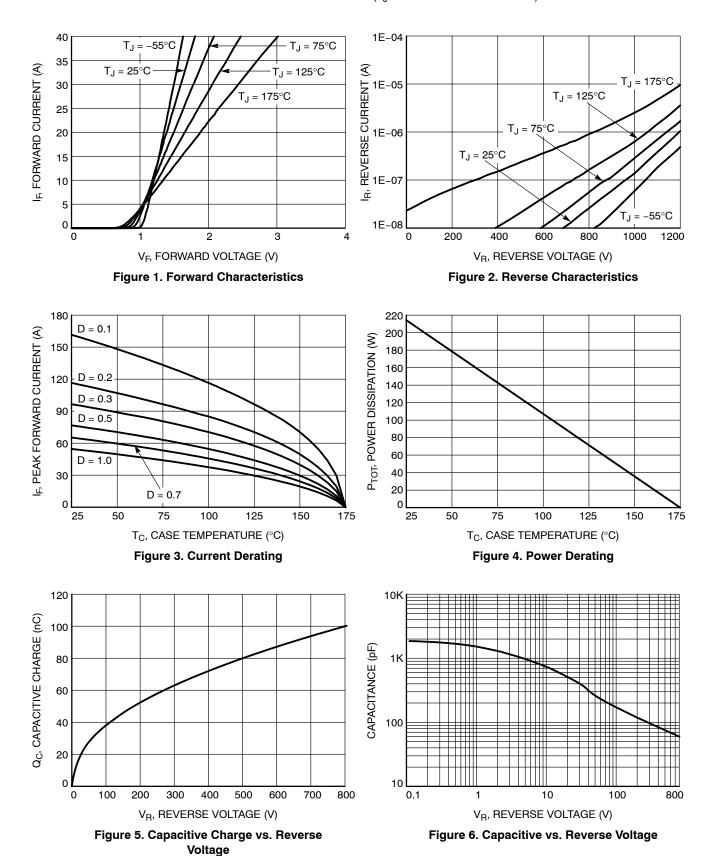
Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 20 A, T <sub>J</sub> = 25°C	-	1.38	1.75	V
		I <sub>F</sub> = 20 A, T <sub>J</sub> = 125°C	_	1.64	-	
		I <sub>F</sub> = 20 A, T <sub>J</sub> = 175°C	-	1.87	-	
I <sub>R</sub>	Reverse Current	V <sub>R</sub> = 1200 V, T <sub>J</sub> = 25°C	-	2.06	200	μΑ
		V <sub>R</sub> = 1200 V, T <sub>J</sub> = 125°C	-	6.25	200	
		V <sub>R</sub> = 1200 V, T <sub>J</sub> = 175°C	-	15.7	200	
$Q_{C}$	Total Capacitive Charge	V = 800 V	-	100	-	nC
С	Total Capacitance	V <sub>R</sub> = 1 V, f = 100 kHz	-	1480	-	pF
		V <sub>R</sub> = 400 V, f = 100 kHz	_	82	_	
		V <sub>R</sub> = 800 V, f = 100 kHz	_	58	_	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## **ORDERING INFORMATION**

Part Number	Top Marking	Package	Shipping
NVDSH20120C	DSH20120C	TO-247-2LD (Pb-Free / Halogen Free)	30 Units / Tube

## TYPICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted)



## **TYPICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ unless otherwise noted)

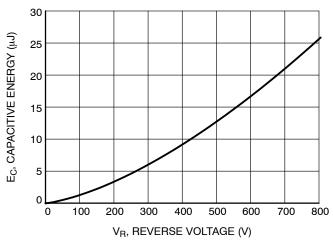


Figure 7. Capacitance Stored Energy

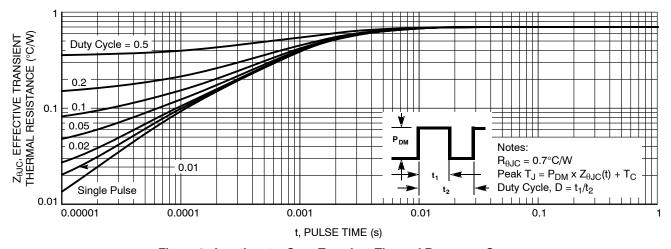
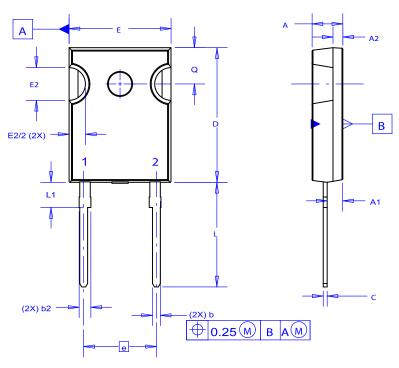


Figure 8. Junction-to-Case Transient Thermal Response Curve

### **PACKAGE DIMENSIONS**

## TO-247-2LD CASE 340DA **ISSUE A**

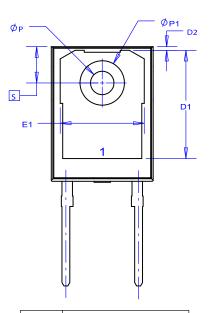


## NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.

  B. ALL DIMENSIONS ARE IN MILLIMETERS.

- C. DRAWING CONFORMS TO ASME Y14.5 2009.
  D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.



DIM	MILLIMETERS				
DIM	MIN	NOM	MAX		
Α	4.58	4.70	4.82		
A1	2.20	2.40	2.60		
A2	1.40	1.50	1.60		
b	1.17	1.26	1.35		
b2	1.53	1.65	1.77		
С	0.51	0.61	0.71		
D	20.32	20.57	20.82		
D1	13.08	?	~		
D2	0.51	0.93	1.35		
Е	15.37	15.62	15.87		
E1	12.81	l	~		
E2	4.96	5.08	5.20		
е	?	11.12	~		
L	15.75	16.00	16.25		
L1	3.69	3.81	3.93		
ØΡ	3.51	3.58	3.65		
ØP1	6.60	6.80	7.00		
Q	5.34	5.46	5.58		
S	5.34	5.46	5.58		

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